

### **N-Channel MOSFET**

#### **Features**

- Low gate threshold voltage low
- Input capacitance
- Fast switching speed
- Low input output leakage
- High Drain-Source voltage rating
- ESD protected (HBM > 2KV)

### **Mechanical Data**

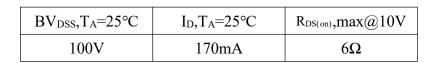
• Case: SOT-23, Molded Plastic

• Case material - UL Flammability Rating

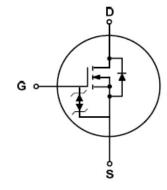
• Terminal Connections: See Diagram

• Marking: SA

• Page 4 Weight: 0.008 grams (approx.)







**SOT-23** 

### **Absolute Maximum Ratings**(T<sub>A</sub>=25°C,unless otherwise noted.)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{ m DS}$	100	V
Drain-Gate Voltage R <sub>GS</sub> ≤20KΩ	V <sub>DGR</sub>	100	V
Gate-source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	170	mA
Drain Current-Pulsed	$I_{\mathrm{DM}}$	680	mA
Maximum Power Dissipation	$P_{D}$	300	mW
Operating Junction Temperature Range	$T_{\mathrm{J}}$	-55~+150	°C
Storage Temperature Range	T <sub>STG</sub>	-55~+150	°C

### **Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to ambient, Max.	$R_{ heta JA}$	417	°C/W

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# **Electrical Characteristics**(T<sub>A</sub>=25°C,unless otherwise noted.)

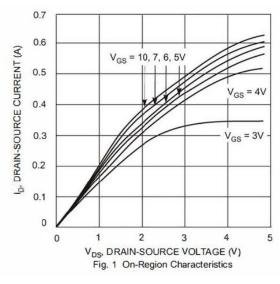
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static Characteristics(1)	,	1		ı		
Drain-Source Breakdown Voltage	$\mathrm{BV}_{\mathrm{DSS}}$	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
Drain-to-Source Leakage Current	$I_{ m DSS}$	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			100	nA
		V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			10	nA
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}$ =±20V, $V_{DS}$ =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	0.8	1.4	2.5	V
Drain-Source On Resistance		V <sub>GS</sub> =10V, I <sub>D</sub> =0.17A			6	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.17A			9	Ω
Forward Transconductance	$g_{\mathrm{fs}}$	V <sub>DS</sub> =10V, I <sub>D</sub> =0.17A, f=1MHz	80	370		mS
Dynamic Characteristics						
Input Capacitance	Ciss	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V, f=1MHz		29	60	pF
Output Capacitance	Coss			10	15	pF
Reverse Capacitance	Crss			2	6	pF
Switching Characteristics						
Turn-On Delay Time	td(on)	$V_{DD}$ =30V, $V_{GS}$ =10V, $I_{D}$ =0.28A, $R_{G}$ =50 $\Omega$		8		nS
Turn-On Rise Time	tr			8		nS
Turn-Off Delay Time	td(off)			13		nS
Turn-Off Fall Time	tf			16		nS
Source-Drain Diode Characteristics			•			
Diode Forward Voltage	$V_{SD}$	V <sub>GS</sub> =0V, I <sub>SD</sub> =0.34A		0.84	1.3	V

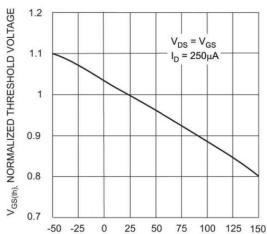
Note: 1. Short duration test pulse used to minimize self-heating effect.

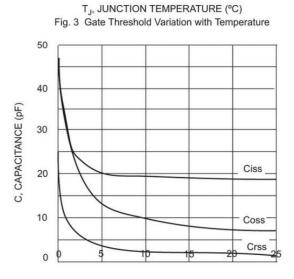
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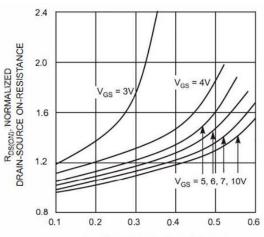


# **Typical Characteristics**

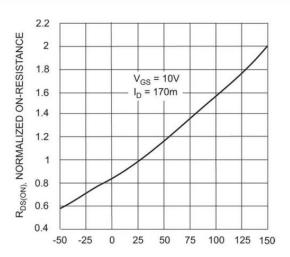








I<sub>D</sub>, DRAIN-SOURCE CURRENT (A)
Fig. 2 On-Resistance Variation with Gate Voltage
and Drain-Source Current



T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Fig. 4 On-Resistance Variation with Temperature

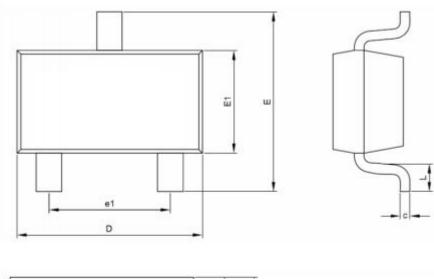
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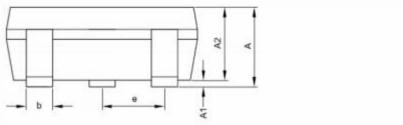


# **Package Information**

# SOT-23

## **Dimensions in mm**





Carrab al	<b>Dimensisons In Millimeters</b>		
Symbol	MIN	MAX	
A	÷	1.12	
A1	0.00	0.10	
A2	0.60	1.02	
D	2.90 BSC		
E	2.40 BSC		
E1	1.20	1.40	
С	0.08	0.25	
b	0.30	0.50	
e	0.95 BSC		
e1	1.90 BSC		
L	0.20	0.60	

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